



Attorney's Docket No. 5308-156

*Image*

*2811*  
*\$*

PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re: Ryu et al.

Serial No.: 09/911,995

Filed: July 24, 2001

Group Art Unit: 2811

Confirmation No.: 5240

Examiner: Gene M. Munson

For: SILICON CARBIDE POWER METAL-OXIDE SEMICONDUCTOR FIELD  
EFFECT TRANSISTORS HAVING A SHORTING CHANNEL AND  
METHODS OF FABRICATING SILICON CARBIDE METAL-OXIDE  
SEMICONDUCTOR FIELD EFFECT TRANSISTORS HAVING A  
SHORTING CHANNEL

Date: February 04, 2004

Commissioner for Patents

PO Box 1450

Alexandria, VA 22313

**SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT**

Sir:

Attached is a list of documents on form PTO-1449 together with copies of each identified document. This Information Disclosure Statement is submitted in accordance with 37 C.F.R. § 1.97(c), before final Office Action or Allowance, whichever is earlier.

The Commissioner is authorized to charge \$180.00 for the fee specified in 37 C.F.R. § 1.17(p) and any additional fee or credit any refund to Deposit Account No. 50-0220.

Respectfully submitted,

Elizabeth A. Stanek

Registration No. 48,568

**Customer No. 20792**

Myers Bigel Sibley & Sajovec

P. O. Box 37428

Raleigh, North Carolina 27627

Telephone: (919) 854-1400

Facsimile: (919) 854-1401

**Certificate of Mailing under 37 CFR 1.8**

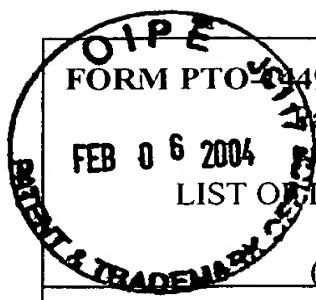
I hereby certify that this correspondence is being deposited with the United States Postal Service with sufficient postage as first class mail in an envelope addressed to: Commissioner for Patents, PO Box 1450, Alexandria, VA 22313-1450 on February 04, 2004.

Ban Youran

02/11/2004 JBALINAN 00000106 500220 09911995

01 FC:1806

180.00 DA

 FORM PTO-449 U.S. Department of Commerce Patent and Trademark Office LIST OF DOCUMENTS CITED BY APPLICANT (Use several sheets if necessary)				Attorney Docket Number: 5308-156		Serial No.: 09/911,995	
				Applicants: Ryu et al.			
				Filing Date: July 24, 2001		Group: 2811	
U. S. PATENT DOCUMENTS							
Examiner Initial		Document Number	Date	Name	Class	Subclass	Filing Date if Appropriate
FOREIGN PATENT DOCUMENTS							
		Document Number	Date	Country	Class	Subclass	Translation Yes   No
OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)							
	1	Williams et al., "Passivation of the 4-H SiC/SiO <sub>2</sub> Interface with Nitric Oxide", <i>Materials Science Forum</i> , Vols. 389-393, 2002, pp. 967-972.					
	2	Chung et al., "Effects of Anneals in Ammonia on the Interface Trap Density Near the Band Edges in 4H-Silicon Carbide Metal-Oxide-Semiconductor Capacitors", <i>Applied Physics Letters</i> , Vol. 77, No. 22, November 27, 2000, pp. 3601-3603.					

EXAMINER \_\_\_\_\_

DATE CONSIDERED \_\_\_\_\_

\*EXAMINER

Initial if reference considered, whether or not citation is in conformance with MPEP 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.